Preferred Devices

Dual General Purpose Transistors

PNP Duals

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-363/SC-88 which is designed for low power surface mount applications.

Features

• These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector – Emitter Voltage	BC856 BC857 BC858	V _{CEO}	-65 -45 -30	V
Collector - Base Voltage	BC856 BC857 BC858	V _{CBO}	-80 -50 -30	V
Emitter - Base Voltage		V _{EBO}	-5.0	V
Collector Current -Continuous		I _C	-100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation Per Device FR-5 Board (Note 1) T _A = 25°C Derate Above 25°C	P _D	380 250 3.0	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	328	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

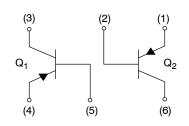
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in



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SOT-363/SC-88 CASE 419B STYLE 1

MARKING DIAGRAM



3x = Specific Device Code x = B, F, G, or L

(See Ordering Information)

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Charac	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS		<u> </u>				
Collector – Emitter Breakdown Voltag (I _C = -10 mA)	BC856 Series	V _(BR) CEO	-65 45	-	_	V
	BC857 Series BC858 Series		-45 -30	-	_ _	
Collector - Emitter Breakdown Voltage		V _{(BR)CES}				V
$(I_C = -10 \mu A, V_{EB} = 0)$	BC856 Series		-80 -50	_	_	
	BC857B Only BC858 Series		-30 -30	-	-	
Collector - Base Breakdown Voltage		V _{(BR)CBO}				V
$(I_C = -10 \mu A)$	BC856 Series		-80	_	_	
	BC857 Series BC858 Series		-50 -30	_ _	_ _	
Emitter – Base Breakdown Voltage		V _{(BR)EBO}				V
$(I_E = -1.0 \mu A)$	BC856 Series	(21.)223	-5.0	_	_	
	BC857 Series		-5.0	_	-	
	BC858 Series		-5.0	-	-	
Collector Cutoff Current ($V_{CB} = -30 \ V_{CB} = -30 \ V_{CB}$	/) /, T _A = 150°C)	I _{CBO}	_	_	–15 –4.0	nA μA
ON CHARACTERISTICS	, 1 <u>A</u> = 100 0)				7.0	μοι
DC Current Gain		h _{FE}				
$(I_C = -10 \mu A, V_{CE} = -5.0 \text{ V})$ BC	C856B, BC857B	"FE	-	150	_	
ВС	C857C, BC858C		-	270	-	
, 32	0856B, BC857B 0857C, BC858C		220 420	290 520	475 800	
Collector - Emitter Saturation Voltage		V _{CE(sat)}				V
$(I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA})$ $(I_C = -100 \text{ mA}, I_B = -5.0 \text{ mA})$			_	-	-0.3 -0.65	
Base – Emitter Saturation Voltage		V _{BE(sat)}			0.00	V
$(I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA})$		V BE(Sat)	_	-0.7	_	
$(I_C = -100 \text{ mA}, I_B = -5.0 \text{ mA})$			-	-0.9	_	
Base – Emitter On Voltage		V _{BE(on)}	0.0		0.75	V
$(I_C = -2.0 \text{ mA}, V_{CE} = -5.0 \text{ V})$ $(I_C = -10 \text{ mA}, V_{CE} = -5.0 \text{ V})$			-0.6 -	-	-0.75 -0.82	
SMALL-SIGNAL CHARACTERISTIC	:S	L		l	l	
Current – Gain – Bandwidth Product (I _C = -10 mA, V _{CE} = -5.0 Vdc, f =	100 MHz)	f _T	100	_	_	MHz
Output Capacitance (V _{CB} = -10 V, f = 1.0 MHz)		C _{ob}	_	_	4.5	pF
Noise Figure ($I_C = -0.2 \text{ mA}, V_{CE} = -5.0 \text{ Vdc}, R_S$ f = 1.0 kHz, BW = 200 Hz)	= 2.0 kΩ,	NF	-	-	10	dB

TYPICAL CHARACTERISTICS - BC856

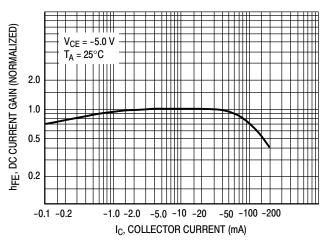


Figure 1. DC Current Gain

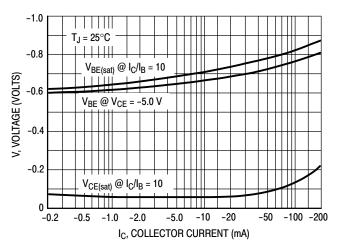


Figure 2. "On" Voltage

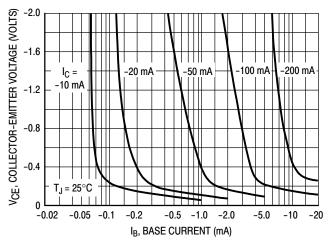


Figure 3. Collector Saturation Region

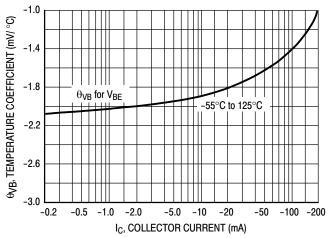


Figure 4. Base-Emitter Temperature Coefficient

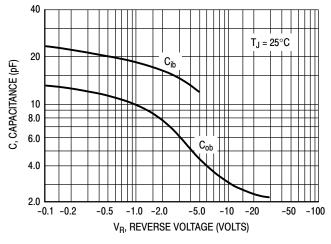


Figure 5. Capacitance

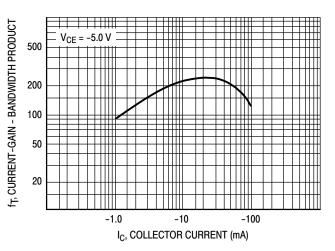
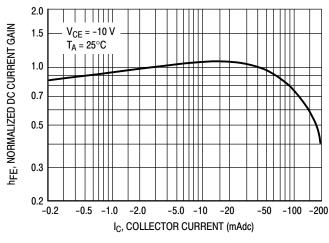


Figure 6. Current-Gain - Bandwidth Product

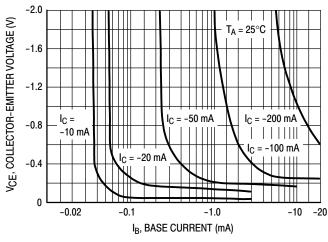
TYPICAL CHARACTERISTICS - BC857/BC858



 $T_A = 25^{\circ}C$ -0.9 V_{BE(sat)} @ I_C/I_B = 10 -0.8-0.7 V, VOLTAGE (VOLTS) $V_{BE(on)} @ V_{CE} = -10 V$ -0.6 -0.5 -0.4 -0.3 -0.2 $V_{CE(sat)} @ I_C/I_B = 10$ -0.1 -0.1 -0.2 -1.0 -2.0 -5.0 -100 -50 IC, COLLECTOR CURRENT (mAdc)

Figure 7. Normalized DC Current Gain

Figure 8. "Saturation" and "On" Voltages



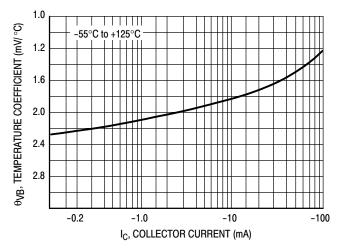
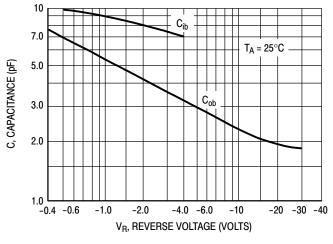


Figure 9. Collector Saturation Region

Figure 10. Base-Emitter Temperature Coefficient



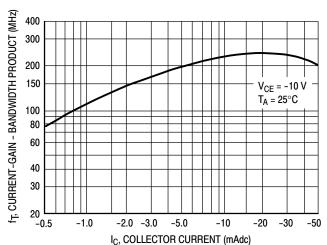


Figure 11. Capacitances

Figure 12. Current-Gain - Bandwidth Product

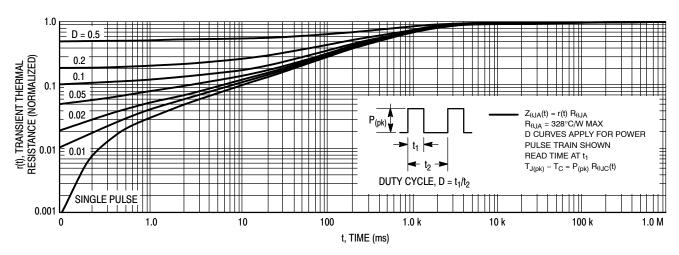


Figure 13. Thermal Response

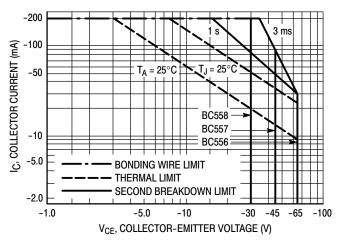


Figure 14. Active Region Safe Operating Area

The safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)} = 150^{\circ}\text{C}$; T_{C} or T_{A} is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

ORDERING INFORMATION

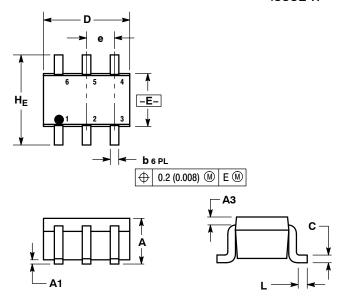
Device	Device Marking	Package	Shipping [†]
BC856BDW1T1G	3B	SOT-363 (Pb-Free)	3,000 / Tape & Reel
BC856BDW1T3G	3B	SOT-363 (Pb-Free)	10,000 / Tape & Reel
BC857BDW1T1G	3F	SOT-363 (Pb-Free)	3,000 / Tape & Reel
BC857CDW1T1G	3G	SOT-363 (Pb-Free)	3,000 / Tape & Reel
BC858CDW1T1G	3L	SOT-363 (Pb-Free)	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363

CASE 419B-02 ISSUE W



NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 - 419B-01 OBSOLETE, NEW STANDARD 419B-02.

	MILLIMETERS		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
А3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
ם	1.80	2.00	2.20	0.070	0.078	0.086
Е	1.15	1.25	1.35	0.045	0.049	0.053
Φ	0.65 BSC		0.026 BSC			
Ь	0.10	0.20	0.30	0.004	0.008	0.012
HF	2.00	2.10	2.20	0.078	0.082	0.086

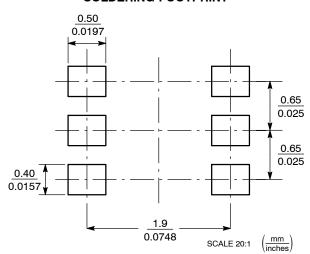
STYLE 1:

- PIN 1. EMITTER 2 2. BASE 2

 - BASE 2 COLLECTOR 1 EMITTER 1

 - 5. BASE 1 6. COLLECTOR 2

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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